H11L1, H11L2, H11L3, H11L4

MICROPROCESSOR COMPATIBLE SCHMITT TRIGGER OPTICALLY COUPLED ISOLATOR

ISOCOM COMPONENTS

ROHS COMPLIANT

DESCRIPTION

The H11L1, 2, 3, 4 series are optically coupled isolators consisting of a Gallium Arsenide infrared emitting diode and a Microprocessor Compatible Schmitt trigger output mounted in a standard 6 pin dual in line package.

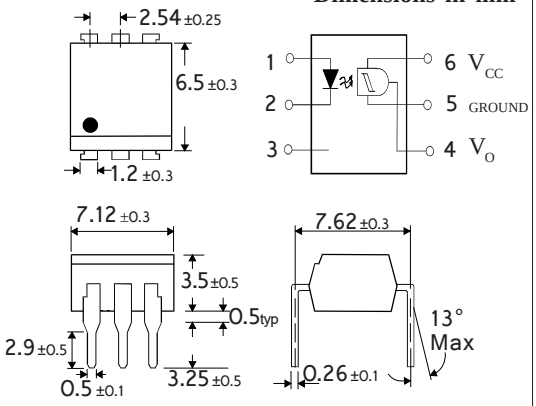
FEATURES

- Options :-
  10mm lead spread - add G after part no.
  Surface mount - add SM after part no.
  Tape&reel - add SMT&R after part no.
- High data rate, 1MHz typical (NRZ)
- Microprocessor compatible drive
- Logic compatible output sinks 16 milliamperes at 0.4 volts maximum
- High Isolation Voltage ($5kV_{RMS}$, $7kV_{PK}$)
- High common mode rejection ratio
- Fast switching : t *rise*, t *fall* = 100nS typical
- Wide supply voltage capability,compatible with all popular logic systems
- Guaranteed On / Off threshold hysteresis

APPLICATIONS

- Logic to logic isolator
- Line receiver-eliminates noise and transient problems
- Programmable current level sensor
- AC to TTL conversion - square wave shaping
- Digital programming of power supplies
- Interfaces computers with peripherals

Dimensions in mm



ABSOLUTE MAXIMUM RATINGS (25°C unless otherwise specified)

Storage Temperature	-40°C to + 125°C
Operating Temperature	-25°C to + 85°C
Lead Soldering Temperature (1/16 inch (1.6mm) from case for 10 secs)	260°C

INPUT DIODE

Forward Current, I_F	50mA
Peak forward current (Pulse width ≤ 100uS, Duty ratio=0.001)	1A
Reverse Voltage, V_R	6V
Power Dissipation (derate linearly 1.41mW / °C above 25°C)	70mW

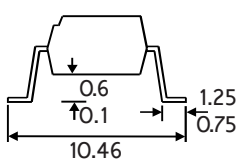
OUTPUT DETECTOR

Output Voltage, Vcc	16V
Supply Voltage, V_{OH}	16V
Output current, I_{OL}	50mA
Power Dissipation (derate linearly 2mW / °C above 25°C)	150mW

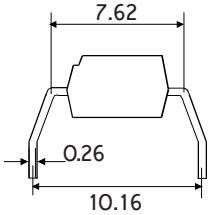
POWER DISSIPATION

Total Power Dissipation (derate linearly 2.94mW/ °C above 25°C)	170mW

OPTION SM
SURFACE MOUNT



OPTION G



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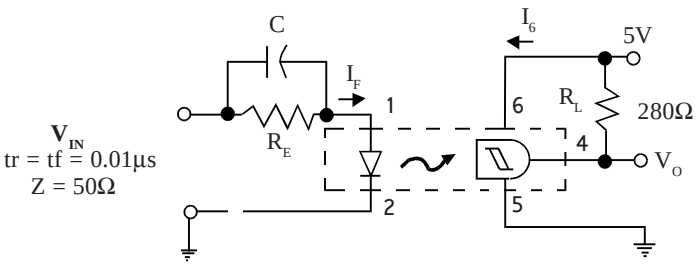
ELECTRICAL CHARACTERISTICS (T_A= 25°C Unless otherwise noted)

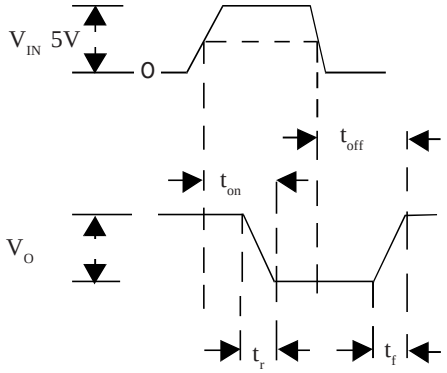
PARAMETER		MIN	TYP	MAX	UNITS	TEST CONDITION
Input	Forward Voltage (V_F)	0.75			V	I_F = 0.3mA
	Forward Voltage (V_F)				1.5 V	I_F = 10mA
	Reverse Current (I_R)			10	µA	V_R = 3V
	Capacitance (C_J)			100	pF	V = 0, f = 1MHz
Output	Operating Voltage Range (V_{CC})	3		15	V	
	Supply Current I_6 (off)		1.6	5	mA	I_F = 0mA, V_{CC} = 5V
	Output Current High (I_{OH})			100	µA	I_F=0mA,V_{CC}=V_O=15V
Coupled	Supply Current I_6 (on)		1.6	5	mA	I_F = 10mA, V_{CC} = 5V
	Output Voltage, Low (V_{OL})			0.4	V	R_L = 270Ω, V_{CC} = 5V
	Turn-on Threshold Current I_F (on)					
	H11L1			1.6	mA	R_L = 270Ω, V_{CC} = 5V
	H11L2			10	mA	R_L = 270Ω, V_{CC} = 5V
	H11L3			5	mA	R_L = 270Ω, V_{CC} = 5V
	H11L4			2	mA	R_L = 270Ω, V_{CC} = 5V
	Turn-off Threshold Current I_F (off)	0.3			mA	R_L = 270Ω, V_{CC} = 5V
	Hysteresis Ratio I_F (off) / I_F (on)	0.5		0.9		R_L = 270Ω, V_{CC} = 5V
	Input to Output Isolation Voltage V_{IS0}	5000			V_{RMS}	See note 1
		7000			V_{PK}	See note 1
	High to Low Propagation time t_{PHL}		1	3	µs	R_E = 280Ω
	Fall Time t_f		0.05	0.5	µs	V_{cc}=5V
	Low to High Propagation time t_{PLH}		2	6	µs	I_F = 4mA
	Rise Time t_r		0.1	0.5	µs	

Note 1 Measured with input leads shorted together and output leads shorted together for 1 minute
Note 2 Special Selections are available on request. Please consult the factory.

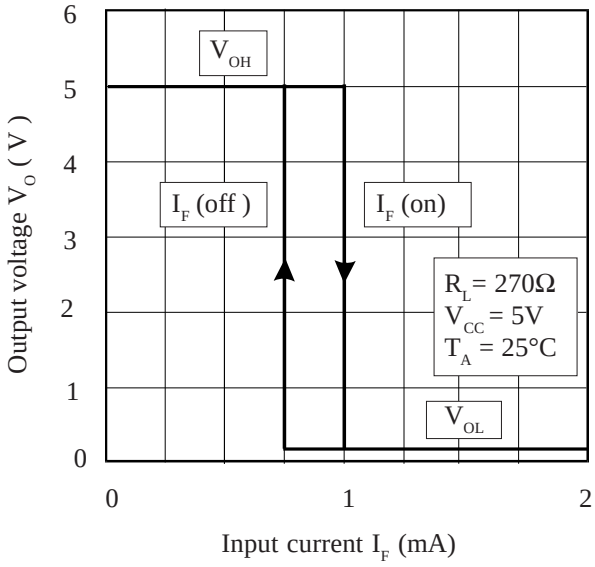
SWITCHING CHARACTERISTICS



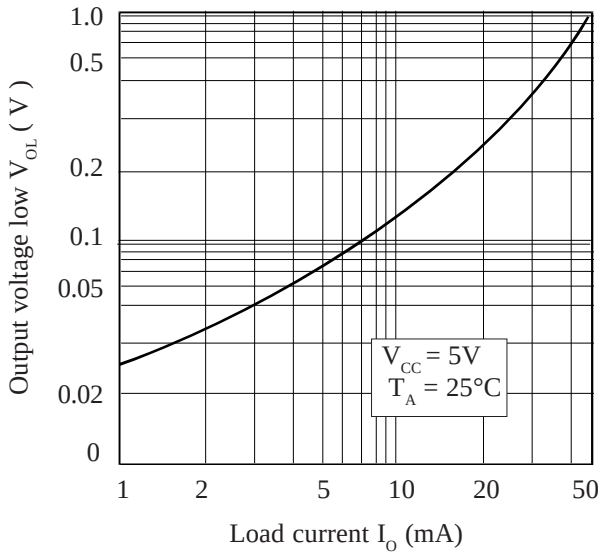
SWITCHING TEST CIRCUIT



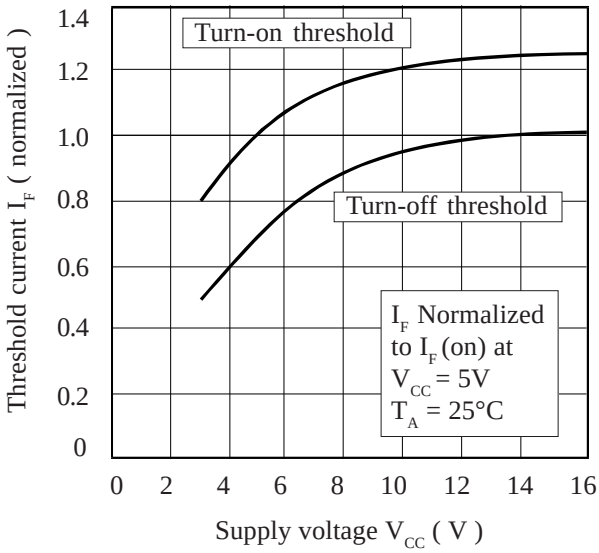
Transfer Characteristics



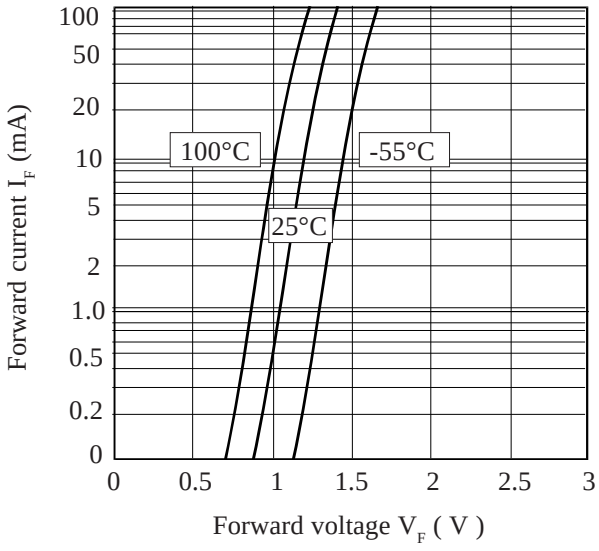
On Voltage vs. Load Current



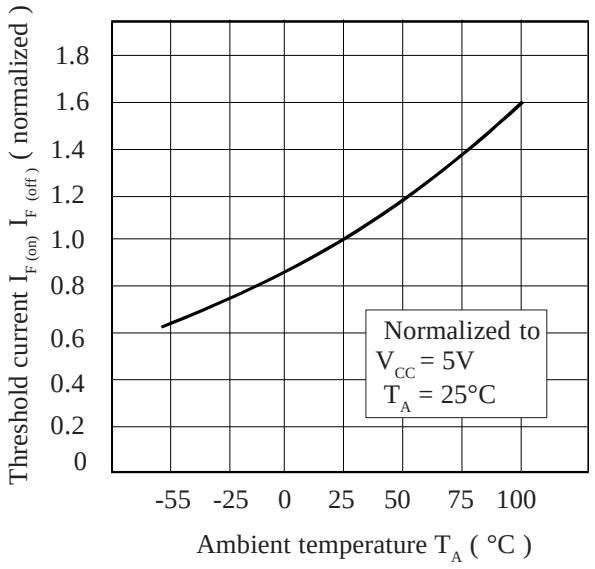
Threshold Current vs. Supply Voltage



Forward Voltage vs. Forward Current



Threshold Current vs. Ambient Temperature



Supply Current vs. Supply Voltage